

SCANNED 21 O.A. 1 PATENT DATE

APPLICATION NO. 09/943187	CONT/PRIOR	CLASS 365	SUBCLASS 102	ART UNIT 2818	EXAMINER J Wong
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APPLICANTS

THE

Method of forming non-volatile resistance variable devices and
method of forming a programmable memory cell of memory circuitry

PTO-204
12/99

ISSUING CLASSIFICATION												
ORIGINAL		CROSS REFERENCE(S)										
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)									
438	102	438	130	84	795	213						
INTERNATIONAL CLASSIFICATION												
	01/06											

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TERMINAL DISCLAIMER

- ☐ The term of this patent subsequent to _____ has been disclaimed.
- ☐ The term of this patent not extend beyond the term of U.S. Patent. No. _____
- ☐ The terminal _____ of this patent have been disclaimed.

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DRAWINGS

Sheets Drwg.	Figs. Drwg.	Print Fig.
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(Assistant Examiner)

(Date _____)

(Primary Examiner)

(Date)

(Legal Instruments Examiner)

(Date)

CLAIMS ALLOWED

Total Claims

Print Claim for O.G.

NOTICE OF ALLOWANCE MAILED

ISSUE FEE

Amount Due

Date Paid

ISSUE BATCH NUMBER

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